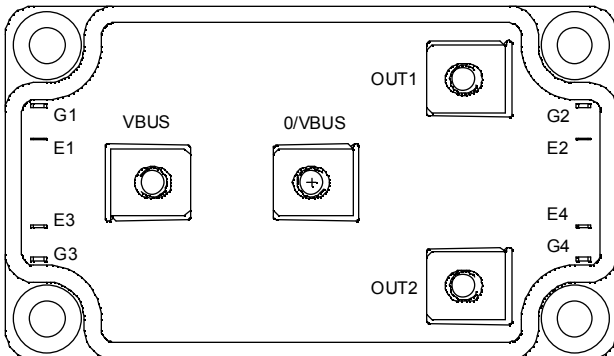
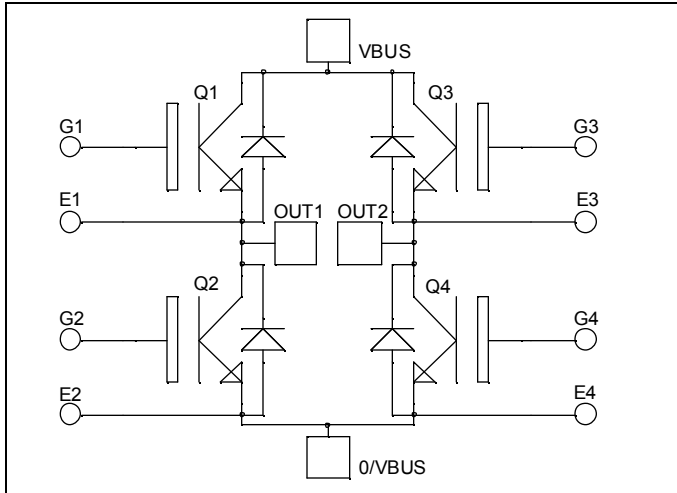


**Full - Bridge  
Trench + Field Stop IGBT®  
Power Module**

**$V_{CES} = 1700V$   
 $I_C = 100A @ T_c = 80°C$**



### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Trench + Field Stop IGBT® Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCESat
- Low profile
- RoHS Compliant

### Absolute maximum ratings

| Symbol    | Parameter                             | Max ratings   | Unit         |
|-----------|---------------------------------------|---------------|--------------|
| $V_{CES}$ | Collector - Emitter Breakdown Voltage | 1700          | V            |
| $I_C$     | Continuous Collector Current          | $T_C = 25°C$  | 150          |
|           |                                       | $T_C = 80°C$  | 100          |
| $I_{CM}$  | Pulsed Collector Current              | $T_C = 25°C$  | 200          |
| $V_{GE}$  | Gate - Emitter Voltage                | $\pm 20$      | V            |
| $P_D$     | Maximum Power Dissipation             | $T_C = 25°C$  | 560          |
| RBSOA     | Reverse Bias Safe Operating Area      | $T_j = 125°C$ | 200A @ 1600V |

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

| <i>Symbol</i> | <i>Characteristic</i>                | <i>Test Conditions</i>                       | <i>Min</i>                | <i>Typ</i> | <i>Max</i> | <i>Unit</i>   |
|---------------|--------------------------------------|--|---------------------------|------------|------------|---------------|
| $I_{CES}$     | Zero Gate Voltage Collector Current  | $V_{GE} = 0\text{V}, V_{CE} = 1700\text{V}$  |                           |            | 350        | $\mu\text{A}$ |
| $V_{CE(sat)}$ | Collector Emitter Saturation Voltage | $V_{GE} = 15\text{V}$<br>$I_C = 100\text{A}$ | $T_j = 25^\circ\text{C}$  | 2.0        | 2.4        | V             |
|               |                                      |  | $T_j = 125^\circ\text{C}$ | 2.4        |            |               |
| $V_{GE(th)}$  | Gate Threshold Voltage               | $V_{GE} = V_{CE}, I_C = 2\text{mA}$          | 5.0                       | 5.8        | 6.5        | V             |
| $I_{GES}$     | Gate – Emitter Leakage Current       | $V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$    |                           |            | 500        | nA            |

**Dynamic Characteristics**

| <i>Symbol</i> | <i>Characteristic</i>        | <i>Test Conditions</i>  | <i>Min</i>                | <i>Typ</i> | <i>Max</i> | <i>Unit</i> |
|---------------|------------------------------|---|---------------------------|------------|------------|-------------|
| $C_{ies}$     | Input Capacitance            | $V_{GE} = 0\text{V}$  |                           | 9          |            | nF          |
| $C_{oes}$     | Output Capacitance           | $V_{CE} = 25\text{V}$   |                           | 0.36       |            |             |
| $C_{res}$     | Reverse Transfer Capacitance | $f = 1\text{MHz}$   |                           | 0.3        |            |             |
| $T_{d(on)}$   | Turn-on Delay Time           | Inductive Switching ( $25^\circ\text{C}$ )<br>$V_{GE} = 15\text{V}$<br>$V_{Bus} = 900\text{V}$<br>$I_C = 100\text{A}$<br>$R_G = 4.7\ \Omega$  |                           | 370        |            | ns          |
| $T_r$         | Rise Time                    |   |                           | 40         |            |             |
| $T_{d(off)}$  | Turn-off Delay Time          |   |                           | 650        |            |             |
| $T_f$         | Fall Time                    |   |                           | 180        |            |             |
| $T_{d(on)}$   | Turn-on Delay Time           | Inductive Switching ( $125^\circ\text{C}$ )<br>$V_{GE} = 15\text{V}$<br>$V_{Bus} = 900\text{V}$<br>$I_C = 100\text{A}$<br>$R_G = 4.7\ \Omega$ |                           | 400        |            | ns          |
| $T_r$         | Rise Time                    |   |                           | 50         |            |             |
| $T_{d(off)}$  | Turn-off Delay Time          |   |                           | 800        |            |             |
| $T_f$         | Fall Time                    |   |                           | 300        |            |             |
| $E_{on}$      | Turn-on Switching Energy     | $V_{GE} = 15\text{V}$<br>$V_{Bus} = 900\text{V}$<br>$I_C = 100\text{A}$<br>$R_G = 4.7\ \Omega$  | $T_j = 125^\circ\text{C}$ | 32         |            | mJ          |
| $E_{off}$     | Turn-off Switching Energy    |   | $T_j = 125^\circ\text{C}$ | 31         |            |             |

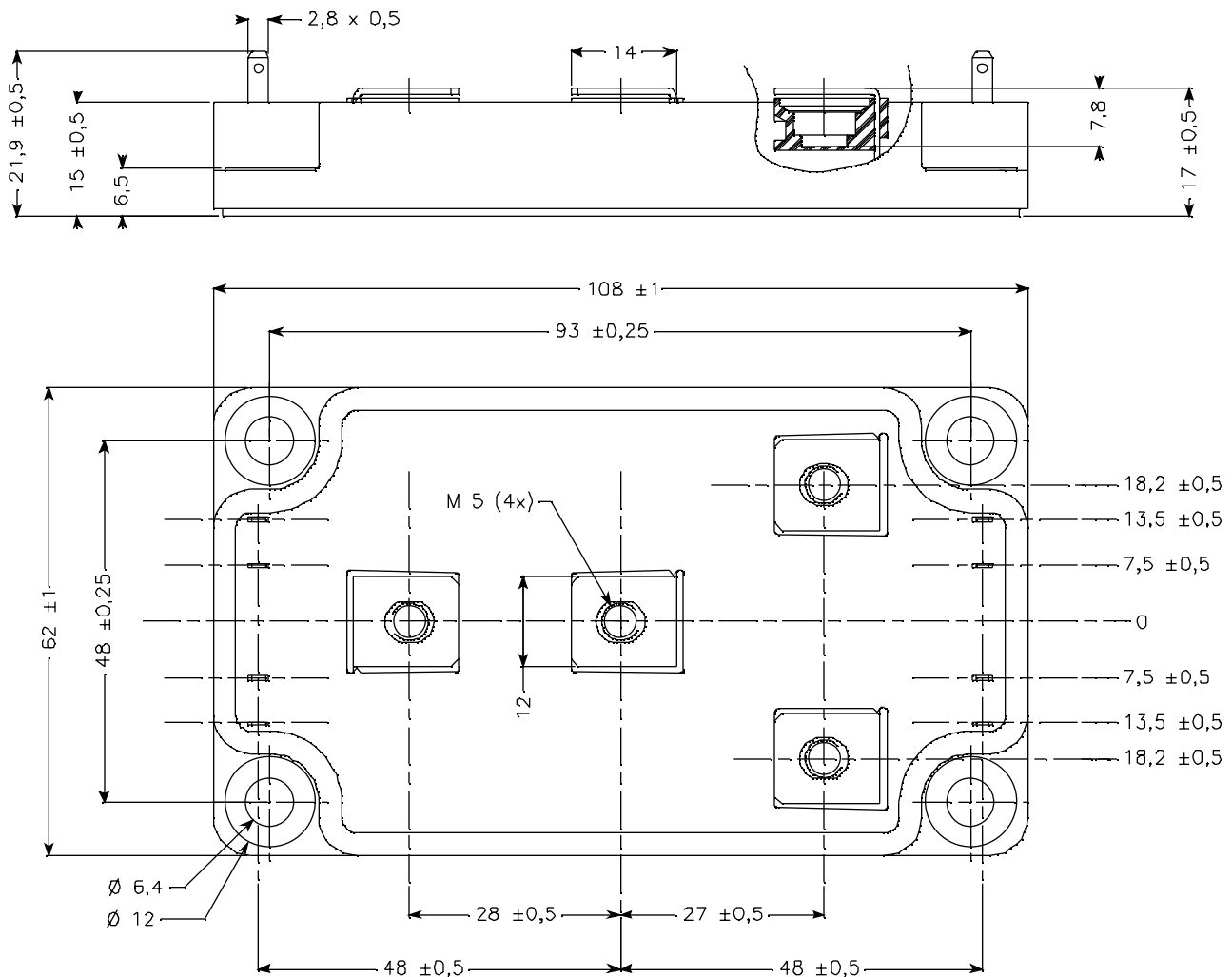
**Diode ratings and characteristics**

| <i>Symbol</i> | <i>Characteristic</i>                   | <i>Test Conditions</i>   | <i>Min</i>                | <i>Typ</i> | <i>Max</i> | <i>Unit</i>   |
|---------------|---|--|---------------------------|------------|------------|---------------|
| $V_{RRM}$     | Maximum Peak Repetitive Reverse Voltage |  | 1700                      |            |            | V             |
| $I_{RM}$      | Maximum Reverse Leakage Current         | $V_R = 1700\text{V}$   | $T_j = 25^\circ\text{C}$  |            | 350        | $\mu\text{A}$ |
|               |   |  | $T_j = 125^\circ\text{C}$ |            | 600        |               |
| $I_F$         | DC Forward Current                      |  |                           | 100        |            | A             |
| $V_F$         | Diode Forward Voltage                   | $I_F = 100\text{A}$  | $T_j = 25^\circ\text{C}$  | 1.8        | 2.2        | V             |
|               |   |  | $T_j = 125^\circ\text{C}$ | 1.9        |            |               |
| $t_{rr}$      | Reverse Recovery Time                   | $I_F = 100\text{A}$<br>$V_R = 900\text{V}$<br>$di/dt = 1600\text{A}/\mu\text{s}$ | $T_j = 25^\circ\text{C}$  | 385        |            | ns            |
|               |   |  | $T_j = 125^\circ\text{C}$ | 490        |            |               |
| $Q_{rr}$      | Reverse Recovery Charge                 |  | $T_j = 25^\circ\text{C}$  | 28         |            | $\mu\text{C}$ |
|               |   |  | $T_j = 125^\circ\text{C}$ | 46         |            |               |
| $E_r$         | Reverse Recovery Energy                 |  | $T_j = 25^\circ\text{C}$  | 12         |            | mJ            |
|               |   |  | $T_j = 125^\circ\text{C}$ | 24         |            |               |

## Thermal and package characteristics

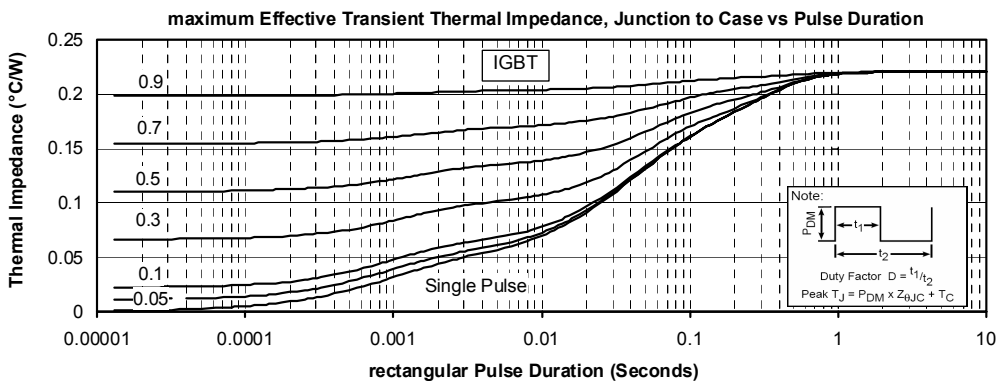
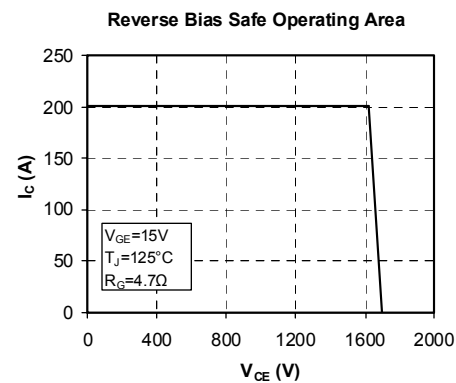
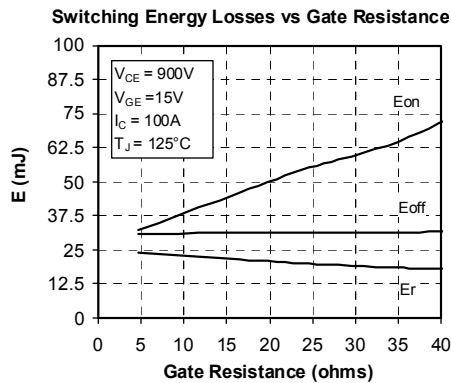
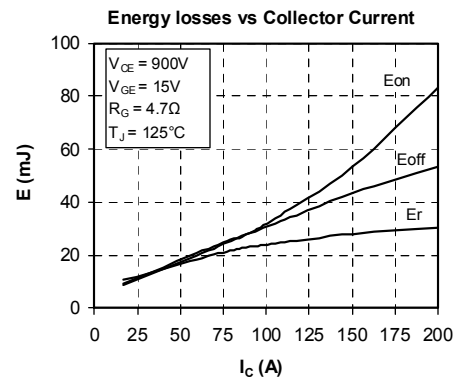
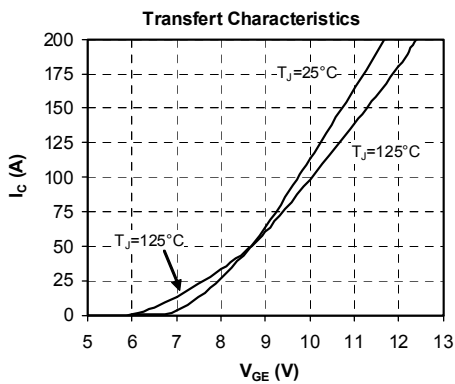
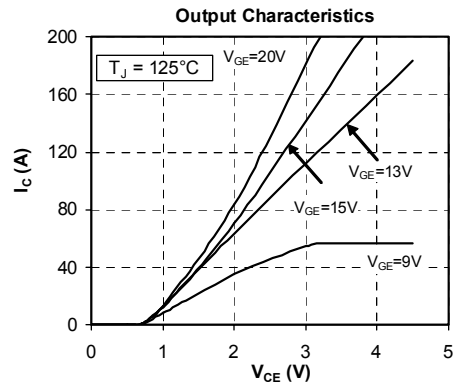
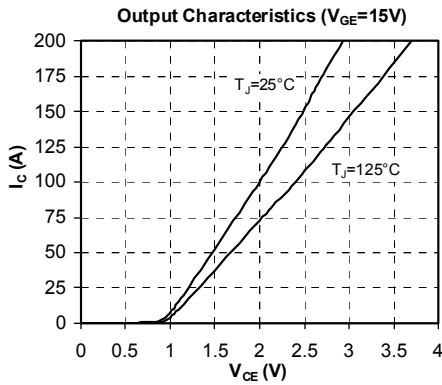
| Symbol            | Characteristic   | Min           | Typ | Max  | Unit |     |
|-------------------|--|---------------|-----|------|------|-----|
| R <sub>thJC</sub> | Junction to Case Thermal Resistance  | IGBT          |     | 0.22 | °C/W |     |
|                   |  | Diode         |     | 0.39 |      |     |
| V <sub>ISOL</sub> | RMS Isolation Voltage, any terminal to case t=1 min, I <sub>isol</sub> <1mA, 50/60Hz | 3500          |     |      | V    |     |
| T <sub>J</sub>    | Operating junction temperature range   | -40           |     | 150  | °C   |     |
| T <sub>STG</sub>  | Storage Temperature Range  | -40           |     | 125  |      |     |
| T <sub>C</sub>    | Operating Case Temperature   | -40           |     | 100  |      |     |
| Torque            | Mounting torque  | To heatsink   | M6  | 3    | 5    | N.m |
|                   |  | For terminals | M5  | 2    | 3.5  |     |
| Wt                | Package Weight   |               |     | 280  | g    |     |

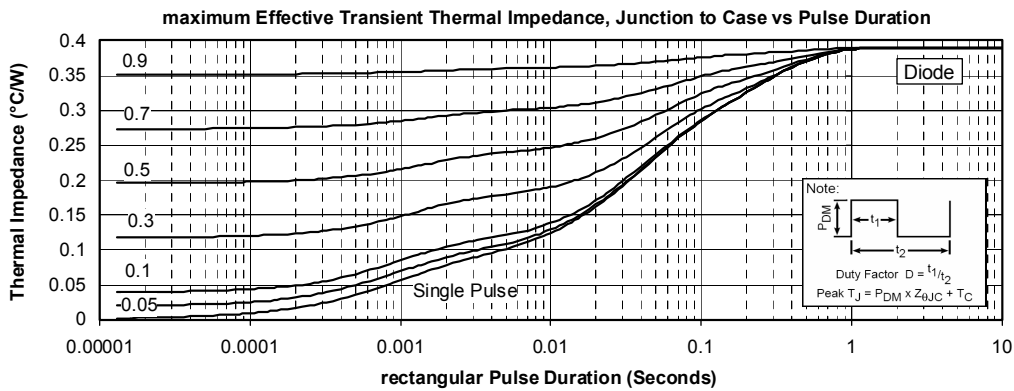
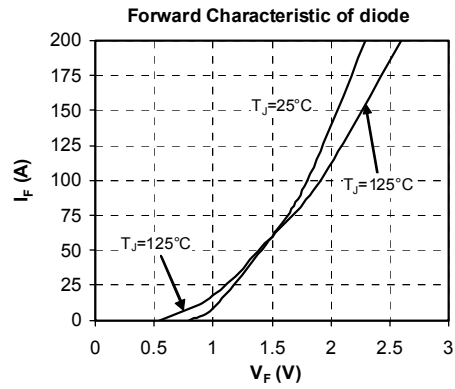
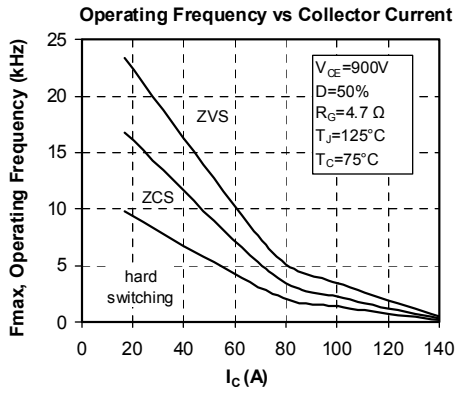
## SP6 Package outline (dimensions in mm)



See application note APT0601 - Mounting Instructions for SP6 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve





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